



# MMBTA42

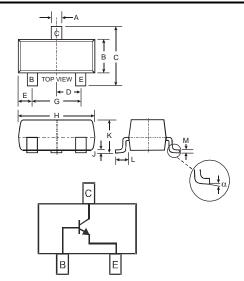
#### NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBTA92)
- Ideal for Low Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 4 and 5)
- Qualified to AEC-Q101 Standards for High Reliability

# **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking (See Page 2): K3M
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approximate)



SOT-23										
Dim	Min	Max								
Α	0.37	0.51								
В	1.20	1.40								
С	2.30	2.50								
D	0.89	1.03								
E	0.45	0.60								
G	1.78	2.05								
Н	2.80	3.00								
J	0.013	0.10								
K	0.903	1.10								
L	0.45	0.61								
М	0.085	0.180								
α	0°	8°								
All Dimensions in mm										

# Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Collector-Base Voltage	$V_{CBO}$	300	V		
Collector-Emitter Voltage	V <sub>CEO</sub>	300	V		
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V		
Collector Current (Note 1) (Note 3)	I <sub>C</sub>	500	mA		
Power Dissipation (Note 1)	P <sub>d</sub>	300	mW		
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	417	°C/W		
Operating and Storage and Temperature Range	T <sub>i</sub> , T <sub>STG</sub>	-55 to +150	°C		

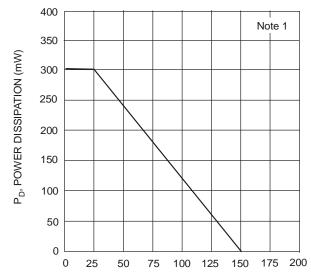
# **Electrical Characteristics** @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition						
OFF CHARACTERISTICS (Note 2)											
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	300	_	V	$I_{C} = 100 \mu A, I_{E} = 0$						
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	300	_	V	$I_C = 1.0 \text{mA}, I_B = 0$						
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	_	V	$I_E = 100 \mu A, I_C = 0$						
Collector Cutoff Current	I <sub>CBO</sub>	_	100	nA	V <sub>CB</sub> = 200V, I <sub>E</sub> = 0						
Collector Cutoff Current	I <sub>EBO</sub>	_	100	nA	$V_{CE} = 6.0V, I_{C} = 0$						
ON CHARACTERISTICS (Note 2)											
		25			$I_C = 1.0 \text{mA}, V_{CE} = 10 \text{V}$						
DC Current Gain	h <sub>FE</sub>	40 40	_	_	$I_C = 10mA, V_{CE} = 10V$						
					$I_C = 30mA, V_{CE} = 10V$						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.5	V	$I_C = 20 \text{mA}, I_B = 2.0 \text{mA}$						
Base- Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	0.9	V	$I_C = 20 \text{mA}, I_B = 2.0 \text{mA}$						
SMALL SIGNAL CHARACTERISTICS											
Output Capacitance	$C_cb$	_	3.0	pF	$V_{CB} = 20V, f = 1.0MHz, I_E = 0$						
Current Gain-Bandwidth Product	f <sub>T</sub>	50	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz						

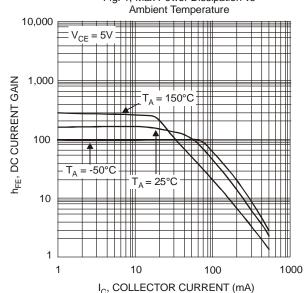
Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. Short duration pulse test used to minimize self-heating effect.
- When operated under collector-emitter saturation conditions within the safe operating area defined by the thermal resistance rating (R<sub>0JA</sub>), power dissipation rating (P<sub>d</sub>) and power derating curve (figure 1).
- 4. No purposefully added lead. Halogen and Antimony Free.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code
  V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.





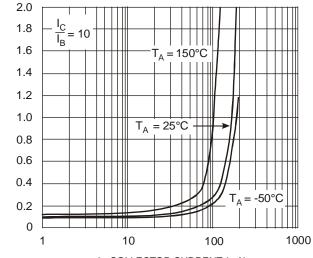
T<sub>A</sub>, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs



Collector Current 100  $V_{CE} = 5V$ f<sub>T</sub>, GAIN BANDWIDTH PRODUCT (MHz) 10 1 10 1

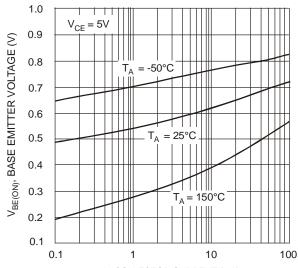
Fig. 3, DC Current Gain vs

 $I_{\rm C}$ , COLLECTOR CURRENT (mA) Fig. 5, Gain Bandwidth Product vs Collector Current



V<sub>CE(SAT)</sub>, COLLECTOR TO EMITTER SATURATION VOLTAGE (V)

 $\rm I_{c}$ , COLLECTOR CURRENT (mA) Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



 $I_{c}$ , COLLECTOR CURRENT (mA) Fig. 4, Base Emitter Voltage vs Collector Current

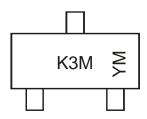


## Ordering Information (Note 6)

Device	Packaging	Shipping			
MMBTA 42-7-F	SOT-23	3000/Tape & Reel			

6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf. Notes:

# **Marking Information**



K3M = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	T	U	V	W	Х	Υ	Z
N	/lonth		Jan	Feb	Mar	Apr	May	Jun	Ju	ı Au	ıg	Sep	Oct	Nov	Dec
Code			1	2	3	4	5	6	7	8	3	9	0	N	D

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